

**Amendments to the Claims:**

1. (Currently amended) A method of manufacturing an integrated circuit device, comprising:

forming an insulation layer that comprises oxygen between upper and lower conductive layers, the insulation layer having a first surface portion that is exposed by the upper and lower conductive layers and a second, non-exposed, surface portion at an interface with the upper conductive layer; and

exposing the insulation layer to a metal precursor that is reactive with oxygen so as to selectively form a first metal oxide layer on substantially only the first surface portion of the insulation layer without forming the first metal oxide layer on the second surface portion of the insulation layer, such that the first metal oxide layer and the second surface portion of the insulation layer do not overlap,

wherein exposing the insulation layer to the metal precursor comprises:  
pulsing the metal precursor over the integrated circuit device; and  
exposing the integrated circuit device to an inert gas.

2. (Canceled)

3. (Currently amended) The method of Claim [[2]] 1, wherein pulsing the metal precursor is performed for a duration of about 0.1 to 2 seconds and at a flow rate of about 50 to 300 sccm.

4. (Currently amended) The method of Claim [[2]] 1, wherein exposing the integrated circuit device to an inert gas is performed for a duration of about 0.1 to 10 seconds and at a flow rate of about 50 to 300 sccm.

5. (Currently amended) The method of Claim [[2]] 1, wherein pulsing the metal precursor comprises:  
pulsing the metal precursor and a carrier gas over the integrated circuit device.

6. (Original) The method of Claim 5, wherein the carrier gas is argon.
7. (Currently amended) The method of Claim [[2]] 1, further comprising:  
thermally treating the integrated circuit device in an oxygen atmosphere using one of  
a rapid thermal processing apparatus and a furnace type thermal processing apparatus.
8. (Original) The method of Claim 7, wherein thermally treating the  
integrated circuit device comprises:  
thermally treating the integrated circuit device in the oxygen atmosphere using a rapid  
thermal processing apparatus at a temperature of about 400 to 600°C for a duration of  
about 10 seconds to 10 minutes.
9. (Original) The method of Claim 1, wherein the metal precursor  
comprises a gas selected from the group of gases consisting of TriMethyl Aluminum  
(TMA), DiMethylAluminum Hydride (DMAH), DiMethylEthylAmine Alane  
(DMEAA), TriIsoButylAluminum (TIBA), TriEthyl Aluminum (TEA), TaCl<sub>5</sub>,  
Ta(OC<sub>2</sub>H<sub>5</sub>)<sub>4</sub>, TiCl<sub>4</sub>, Ti(OC<sub>2</sub>H<sub>5</sub>)<sub>4</sub>, ZrCl<sub>4</sub>, HfCl<sub>4</sub>, Nb(OC<sub>2</sub>H<sub>5</sub>)<sub>5</sub>, Mg(thd)<sub>2</sub>, Ce(thd)<sub>3</sub>,  
and Y(thd)<sub>3</sub>, wherein thd is given by the following structural formula:
10. (Previously presented) The method of Claim 1, wherein exposing the  
insulation layer to the metal precursor is performed at a temperature of about 100 to  
400°C and at a pressure of about 0.1 to 1 torr.
11. (Original) The method of Claim 1, wherein the insulation layer  
comprises a capacitor dielectric layer.
12. (Original) The method of Claim 1, wherein the insulation layer  
comprises a material selected from the group of materials consisting of: TiO<sub>2</sub>, SiO<sub>2</sub>,

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Ta<sub>2</sub>O<sub>5</sub>, Al<sub>2</sub>O<sub>3</sub>, BaTiO<sub>3</sub>, SrTiO<sub>3</sub>, (Ba, Sr)TiO<sub>3</sub>, Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>, PbTiO<sub>3</sub>, PZT((Pb, La)(Zr, Ti)O<sub>3</sub>), and (SrBi<sub>2</sub>Ta<sub>2</sub>O<sub>9</sub>)(SBT).

13. (Original) The method of Claim 1, further comprising:  
encapsulating the first metal oxide layer and the insulation layer in a second metal oxide layer.